

# 2MBI300VH-120-50

**IGBT Modules** 

# **IGBT MODULE (V series)** 1200V / 300A / 2 in one package

#### Features

High speed switching Voltage drive Low Inductance module structure

#### Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines



#### Maximum Ratings and Characteristics

Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items		Symbols	Conditions		Maximum ratings	Units	
	Collector-Emitter voltage	Vces			1200	V	
Inverter	Gate-Emitter voltage	V <sub>GES</sub>			±20	V	
	Collector current	Ic	Continuous	Tc=100°C	300		
				Tc=25°C	360		
		Ic pulse	1ms		600	А	
		-lc			300		
		-lc pulse	1ms		600		
	Collector power dissipation	Pc	1 device		1600	W	
Junction temperature		Tj			175		
Operating junction temperature (under switching conditions)		Tjop			150	°C	
Case temperature		Tc			125	C	
St	orage temperature	Tstg			-40 ~ +125		
Isc	plation voltage between terminal and copper base (*1)	Viso	AC : 1min.		2500	VAC	
Screw torque Mounting (*2)					6.0	NI m	
30	Terminals (*3)	-			5.0	N m	

Note \*1: All terminals should be connected together during the test. Note \*2: Recommendable Value : 3.0-6.0 Nm (M5 or M6) Note \*3: Recommendable Value : 2.5-5.0 Nm (M6)

● Electrical characteristics (at Tj= 25°C unless otherwise specified)

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enis	Symbols	Conditions		min.	typ.	max.	Units
Zero gate voltage collector current	Ices	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 1200V		-	-	2.0	mA
Gate-Emitter leakage current	Iges	$V_{CE} = 0V, V_{GE} = \pm 20V$		-	-	400	nA
Gate-Emitter threshold voltage	V <sub>GE (th)</sub>	V <sub>CE</sub> = 20V, I <sub>C</sub> = 300mA	6.0	6.5	7.0	V	
Collector-Emitter saturation voltage	l <sub>V</sub>	V <sub>GE</sub> = 15V I <sub>C</sub> = 300A	Tj=25°C	-	1.95	2.40	V
	V <sub>CE (sat)</sub> (terminal)		Tj=125°C	-	2.25	-	
	(terrillial)		Tj=150°C	-	2.30	-	
	V		Tj=25°C	-	1.75	2.10	
	V <sub>CE</sub> (sat)		Tj=125°C	-	2.05	-	
	(chip)		Tj=150°C	-	2.10	-	
Internal gate resistance	R <sub>g(int)</sub>	-		-	2.5	-	Ω
Input capacitance	Cies	$V_{CE} = 10V$ , $V_{GE} = 0V$ , $f = 1MHz$		-	24.1	-	nF
Turn-on time	ton	V <sub>cc</sub> = 600V L <sub>s</sub> = 30nH		-	0.60	-	
	tr	Ic = 300A		-	0.20	-	
	tr (i)	$V_{GE} = \pm 15V$ $R_G = 1.8\Omega$		-	0.05	-	µsec
Turn-off time	toff			-	0.80	-	
	tf	Tj = 150°C	- 0.0				]
Forward on voltage	VF	V <sub>GE</sub> = 0V I <sub>F</sub> = 300A	Tj=25°C	-	1.90	2.35	V
	(terminal)		Tj=125°C	-	2.05	-	
	(terrillial)		Tj=150°C	-	2.00	-	
	VF		Tj=25°C	-	1.70	2.15	
			Tj=125°C	-	1.85	-	
	(chip)		Tj=150°C	-	1.80	-	
Reverse recovery time	trr	I <sub>F</sub> = 300A		-	0.15	-	µsec

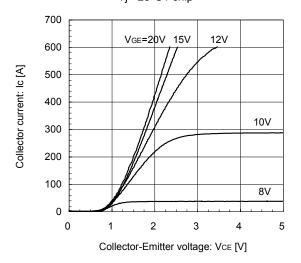
#### Thermal resistance characteristics

	Symbols		Characteristics			Units
Items		Conditions				
			min.	typ.	max.	
Thermal resistance (1device)	Rth(j-c)	IGBT	-	-	0.093	°C/W
Thermal resistance (Tuevice)		FWD	-	-	0.150	
Contact thermal resistance (1device) (*4)	Rth(c-f)	with Thermal Compound	-	0.0125	-	

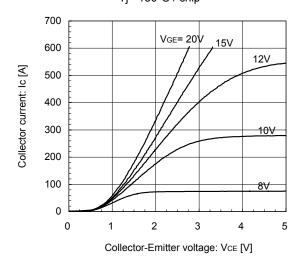
Note \*4: This is the value which is defined mounting on the additional cooling fin with thermal compound.

#### ■ Characteristics (Representative)

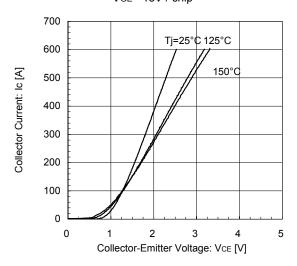
Collector current vs. Collector-Emitter voltage (typ.) Tj= 25°C / chip



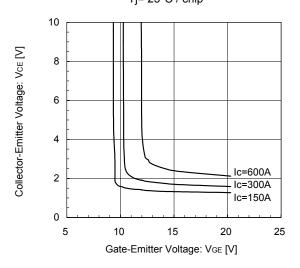
Collector current vs. Collector-Emitter voltage (typ.) Tj= 150°C / chip



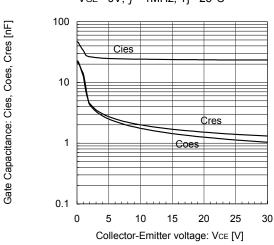
Collector current vs. Collector-Emitter voltage (typ.) VGE= 15V / chip



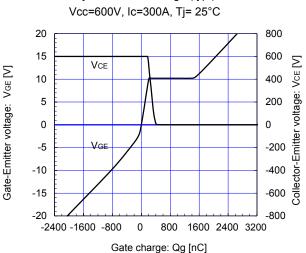
Collector-Emitter voltage vs. Gate-Emitter voltage (typ.) Tj= 25°C / chip



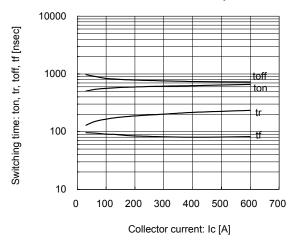
Gate Capacitance vs. Collector-Emitter Voltage (typ.) VGE= 0V, f= 1MHz, Tj= 25°C



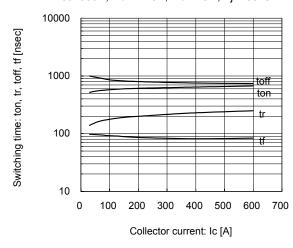
Dynamic Gate Charge (typ.)



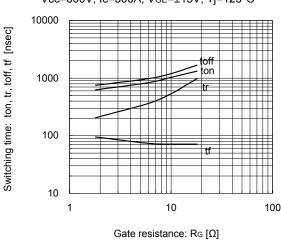
Switching time vs. Collector current (typ.) Vcc=600V, VgE= $\pm$ 15V, Rg=1.8 $\Omega$ , Tj=125°C



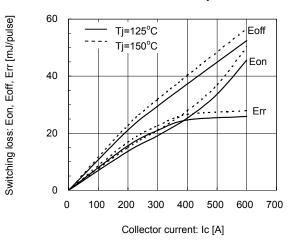
Switching time vs. Collector current (typ.) Vcc=600V,  $VgE=\pm15V$ ,  $Rg=1.8\Omega$ ,  $Tj=150^{\circ}C$ 



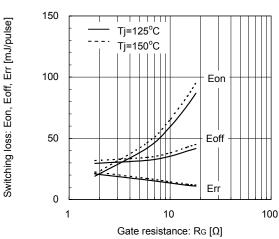
Switching time vs. Gate resistance (typ.) Vcc=600V, Ic=300A, VgE=±15V, Tj=125°C



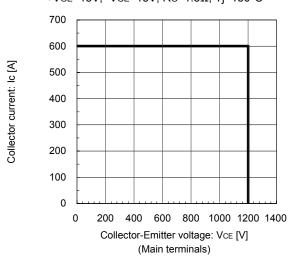
Switching loss vs. Collector current (typ.) Vcc=600V, VgE= $\pm$ 15V, Rg=1.8 $\Omega$ , Tj=125°C, 150°C



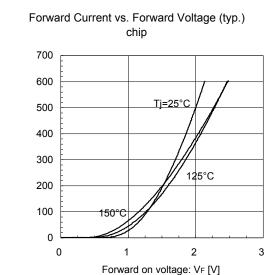
Switching loss vs. Gate resistance (typ.) Vcc=600V, Ic=300A, VGE=±15V, Tj=125°C, 150°C

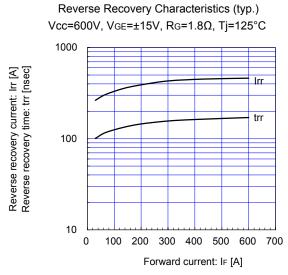


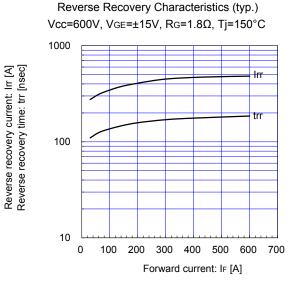
Reverse bias safe operating area (max.) +V<sub>GE</sub>=15V, -V<sub>GE</sub>=15V, R<sub>G</sub>=1.8Ω, Ti=150°C

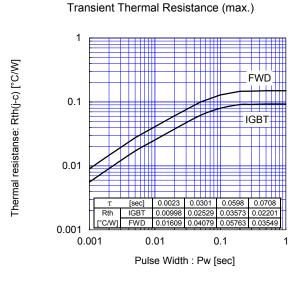


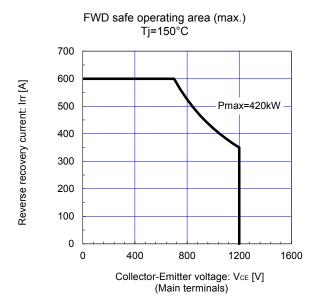
Forward current: IF [A]





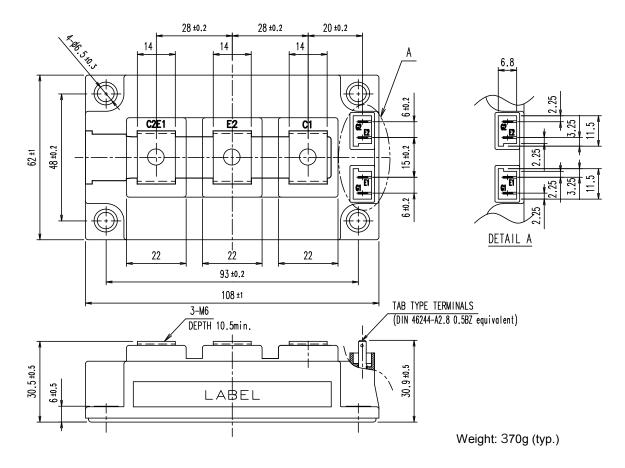




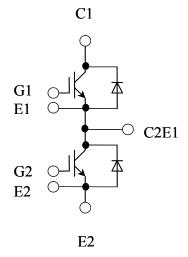


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### ■ Outline Drawings (Unit: mm)



## **■** Equivalent Circuit



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